

## **Features**

- Single-Supply Operation from +1.8V ~ +5.5V
- Rail-to-Rail Input / Output
- Gain-Bandwidth Product: 1.8MHz (Typ@25°C)
- Low Input Bias Current: 20pA (Typ@25°C)
- Low Offset Voltage: 30µV (Max@25°C)
- Quiescent Current: 180µA per Amplifier (Typ)
- Operating Temperature: -45°C ~ +125°C
- Zero Drift: 0.01µV/°C (Typ)

# **General Description**

- Embedded RF Anti-EMI Filter
- Small Package:
- BMD8551 Available in SOT23-5 and SOP-8 Packages

The BMD8551 amplifier is single/dual/quad supply, mi cro-power, zero-drift CMOS operational amplifiers, the amplifiers offer bandwidth of 1.8MHz, rail-to-rail inputs and outputs, and single-supply operation from 1.8V to 5.5V. BMD8551 uses chopper stabilized technique to provide very low offset voltage (less than 30µV maximum) and near zero drift over temperature. Low quiescent supply current of 180µA per amplifier and very low input bias current of 20pA make the devices an ideal choice for low offset, low power consumption and high impedance applications. The BMD8551 offers excellent CMRR without the crossover associated with traditional complementary input stages. This design results in superior performance for driving analog-to-digital converters (ADCs) without degradation of differential linearity.

# Applications

- Transducer Application
- Temperature Measurements
- Electronics Scales

# **Pin Configuration**

- Handheld Test Equipment
- Battery-Powered Instrumentation

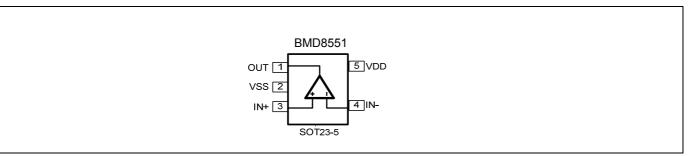


Figure 1. Pin Assignment Diagram





## **Absolute Maximum Ratings**

Condition	Min	Мах		
Power Supply Voltage (V <sub>DD</sub> to Vss)	-0.5V	+7.5V		
Analog Input Voltage (IN+ or IN-)	Vss-0.5V	V <sub>DD</sub> +0.5V		
PDB Input Voltage	Vss-0.5V	+7V		
Operating Temperature Range	-45°C	+125°C		
Junction Temperature	+1	60°C		
Storage Temperature Range	-55°C	+150°C		
Lead Temperature (soldering, 10sec)	+2	60°C		
Package Thermal Resistance (T <sub>A</sub> =+25℃)				
SOP-8, θ <sub>JA</sub>	12!	5°C/W		
MSOP-8, θ <sub>JA</sub>	216	216°C/W		
SOT23-5, θ <sub>JA</sub>	190	190°C/W		
ESD Susceptibility				
НВМ	6	6KV		
MM	4	400V		

**Note:** Stress greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

# **Package/Ordering Information**

MODEL	CHANNEL	ORDER NUMBER	PACKAGE DESCRIPTION	PACKAGE OPTION	MARKING INFORMATION
BMD8551	Single	BDM8551-TR	SOT23-5	Tape and Reel,3000	8551



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## **Electrical Characteristics**

(V\_S = +5V, V\_{CM} = +2.5V, V\_O = +2.5V, T\_A = +25  $^\circ \! \mathbb{C}$  , unless otherwise noted.)

PARAMETER	CONDITIONS M		TYP	MAX	UNITS
INPUT CHARACTERISTICS		•	1		•
Input Offset Voltage (V <sub>OS</sub> )			1	30	μV
Input Bias Current (I <sub>B</sub> )			20		pА
Input Offset Current (I <sub>OS</sub> )			10		pА
Common-Mode Rejection Ratio (CMRR)	V <sub>CM</sub> = 0V to 5V		110		dB
Large Signal Voltage Gain ( A <sub>VO</sub> )	$R_L$ = 10k $\Omega$ , $V_O$ = 0.3V to 4.7V		145		dB
Input Offset Voltage Drift ( $\Delta V_{OS}/\Delta_T$ )			10	50	nV/℃
OUTPUT CHARACTERISTICS					•
	$R_L$ = 100k $\Omega$ to - V <sub>S</sub>		4.998		V
Output Voltage High (V <sub>OH</sub> )	$R_L$ = 10k $\Omega$ to - V <sub>S</sub>		4.994		V
	$R_L$ = 100k $\Omega$ to + V <sub>S</sub>		2		mV
Output Voltage Low (V <sub>OL</sub> )	$R_L = 10k\Omega$ to + V <sub>S</sub>		5		mV
Short Circuit Limit (I <sub>SC</sub> )	$R_L$ =10 $\Omega$ to - V <sub>S</sub>		60		mA
Output Current (I <sub>O</sub> )			65		mA
POWER SUPPLY					•
Power Supply Rejection Ratio (PSRR)	Rejection Ratio (PSRR) $V_{\rm S}$ = 2.5V to 5.5V		115		dB
Quiescent Current (I <sub>Q</sub> )	$V_0 = 0V, R_L = 0\Omega$		180		μA
DYNAMIC PERFORMANCE					
Gain-Bandwidth Product (GBP)	G = +100		1.8		MHz
Slew Rate (SR)	R <sub>L</sub> = 10kΩ		0.95		V/µs
Overload Recovery Time			0.10		ms
NOISE PERFORMANCE					
Voltage Noise (e <sub>n</sub> p-p)	0Hz to 10Hz		0.3		$\mu V_{P\text{-}P}$
Voltage Noise Density (en)	f = 1kHz		38		$nV/\sqrt{H_2}$

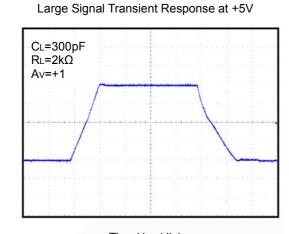


Output Voltage (1V/div)

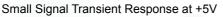
Output Voltage (50mV/div)

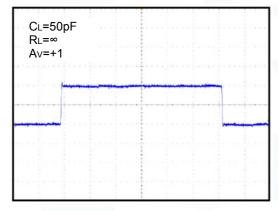
# **BDM8551**

# **Typical Performance characteristics**

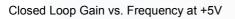


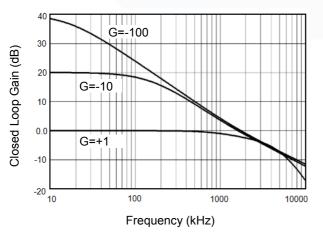
Time(4µs/div)

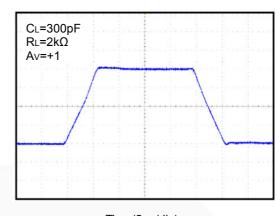




Time(4µs/div)



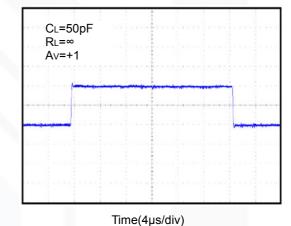




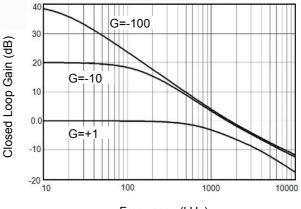
Large Signal Transient Response at +2.5V

Time(2µs/div)

Small Signal Transient Response at +2.5V







Frequency (kHz)

# Output Voltage (500mV/div)

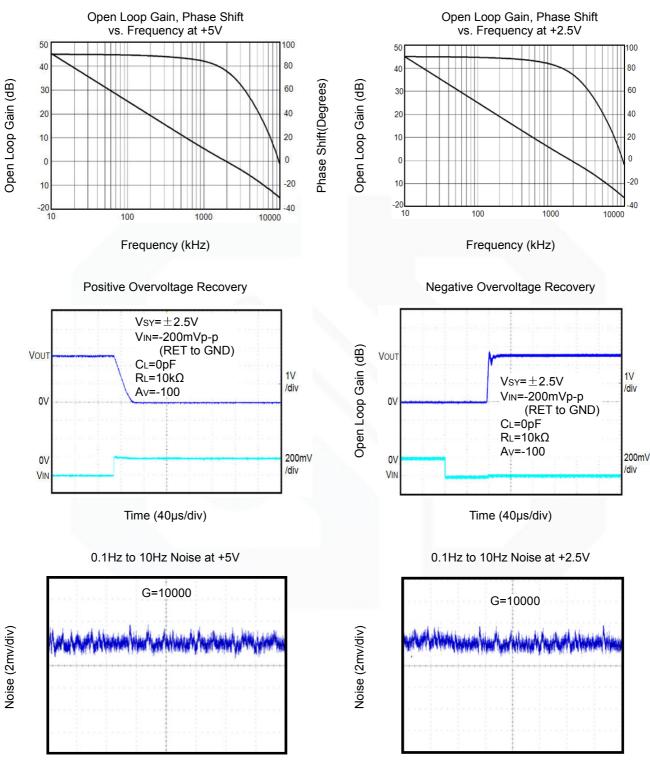
Output Voltage (50mV/div)



# **BDM8551**

Phase Shift(Degrees)

## **Typical Performance characteristics**



Time (10s/div)

Time (10s/div)



**BDM8551** 

## **Application Note**

#### Size

BMD8551 series op amps are unity-gain stable and sui table for a wide range of general-purpose applications. The small footprints of the BMD8551 series packages save space on printed circuit boards and enable the design of smaller electronic products.

#### **Power Supply Bypassing and Board Layout**

BMD8551 series operates from a single 1.8V to 5.5V supply or dual  $\pm 0.9V$  to  $\pm 2.75V$  supplies. For best performance, a  $0.1\mu$ F ceramic capacitor should be placed close to the V<sub>DD</sub> pin in single supply operation. For dual supply operation, both V<sub>DD</sub> and V<sub>SS</sub> supplies should be bypassed to ground with separate  $0.1\mu$ F ceramic capacitors.

#### **Low Supply Current**

The low supply current (typical 180µA per channel) of BMD8551 series will help to maximize battery life . They are ideal for battery powered systems.

#### **Operating Voltage**

BDM8551 series operate under wide input supply voltage (1.8V to 5.5V). In addition, all temperature specifications apply from -40 °C to +125 °C. Most behavior remains unchanged throughout the full operating voltage range. These guarantees ensure operation throughout the single Li-lon battery lifetime.

#### **Rail-to-Rail Input**

The input common-mode range of BDM8551 series extends 100mV beyond the supply rails ( $V_{SS}$ -0.1V to  $V_{DD}$ +0.1V). This is achieved by using complementary input stage. For normal operation, inputs should be limited to this range.

#### **Rail-to-Rail Output**

Rail-to-Rail output swing provides maximum possible dynamic range at the output. This is particularly important when operating in low supply voltages. The output voltage of BDM8551 series can typically swing to less than 5mV from supply rail in light resistive loads (>100k $\Omega$ ), and 60mV of supply rail in moderate resistive loads (10k $\Omega$ ).

#### **Capacitive Load Tolerance**

The BDM8551 family is optimized for bandwidth and speed, not for driving capacitive loads. Output capacitance will create a pole in the amplifier's feedback path, leading to excessive peaking and potential oscillation. If dealing with load capacitance is a requirement of the application, the two strategies to consider are (1) using a small resistor in series with the amplifier's output and the load capacitance and (2) reducing the bandwidth of the amplifier's feedback loop by increasing the overall noise gain. Figure 2. shows a unity gain follower using the series resistor strategy. The resistor isolates the output from the capacitance and, more importantly, creates a zero in the feedback path that compensates for the pole created by the output capacitance.

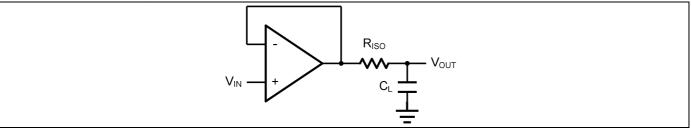


Figure 2. Indirectly Driving a Capacitive Load Using Isolation Resistor



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**BDM8551** 

The bigger the  $R_{ISO}$  resistor value, the more stable  $V_{OUT}$  will be. However, if there is a resistive load  $R_L$  in parallel with the capacitive load, a voltage divider (proportional to  $R_{ISO}/R_L$ ) is formed, this will result in a gain error.

The circuit in Figure 3 is an improvement to the one in Figure 2.  $R_F$  provides the DC accuracy by feed-forward the V<sub>IN</sub> to  $R_L$ .  $C_F$  and  $R_{ISO}$  serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving the phase margin in the overall feedback loop. Capacitive drive can be increased by increasing the value of  $C_F$ . This in turn will slow down the pulse response.

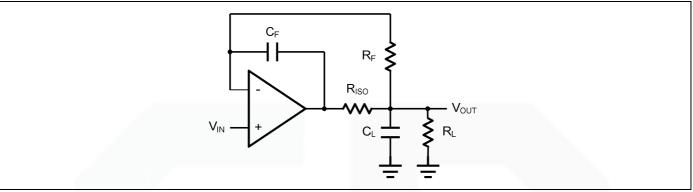


Figure 3. Indirectly Driving a Capacitive Load with DC Accuracy



**BDM8551** 

# **Typical Application Circuits**

#### **Differential amplifier**

The differential amplifier allows the subtraction of two input voltages or cancellation of a signal common the two inputs. It is useful as a computational amplifier in making a differential to single-end conversion or in rejecting a common mode signal. Figure 4. shown the differential amplifier using BDM8551.

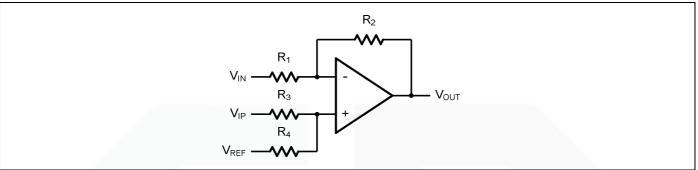


Figure 4. Differential Amplifier

$$V_{\text{OUT}} = \left(\frac{R_1 + R_2}{R_3 + R_4}\right) \frac{R_4}{R_1} V_{\text{IN}} - \frac{R_2}{R_1} V_{\text{IP}} + \left(\frac{R_1 + R_2}{R_3 + R_4}\right) \frac{R_3}{R_1} V_{\text{REF}}$$

If the resistor ratios are equal (i.e.  $R_1=R_3$  and  $R_2=R_4$ ), then

$$V_{\rm OUT} = \frac{R_2}{R_1} (V_{\rm IP} - V_{\rm IN}) + V_{\rm REF}$$

#### **Low Pass Active Filter**

The low pass active filter is shown in Figure 5. The DC gain is defined by  $-R_2/R_1$ . The filter has a -20dB/decade roll-off after its corner frequency  $f_c=1/(2\pi R_3 C_1)$ .

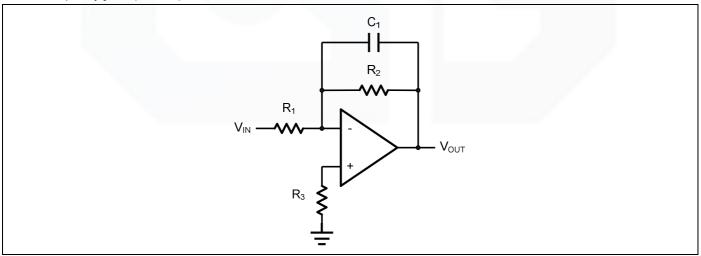


Figure 5. Low Pass Active Filter

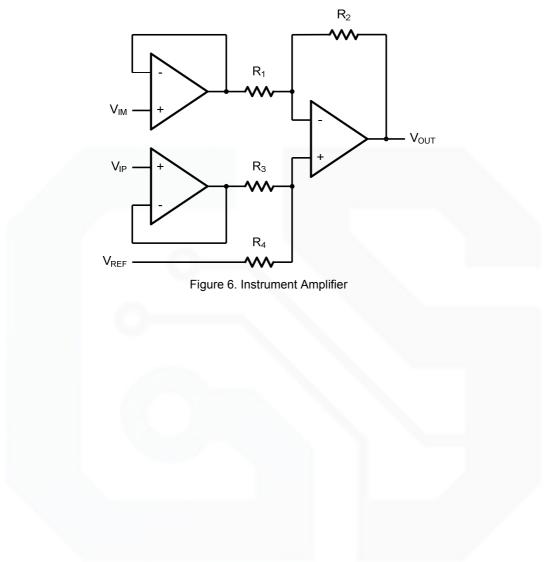


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#### **Instrumentation Amplifier**

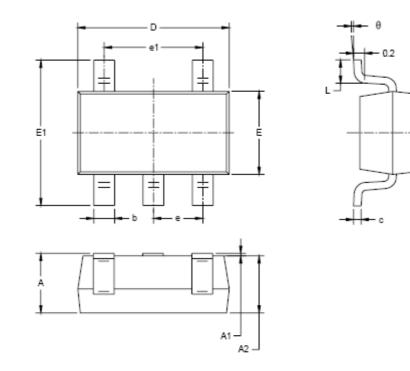
The triple BDM8551 can be used to build a three-op-amp instrumentation amplifier as shown in Figure 6. The amplifier in Figure 6 is a high input impedance differential amplifier with gain of  $R_2/R_1$ . The two differential voltage followers assure the high input impedance of the amplifier.





# **Package Information**

#### SOT23-5



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
с	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950 BSC		0.037 BSC	
e1	1.900 BSC		0.075 BSC	
L	0.300	0.600	0.012	0.024
e	0°	8°	0°	8°

# **BDM8551**

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